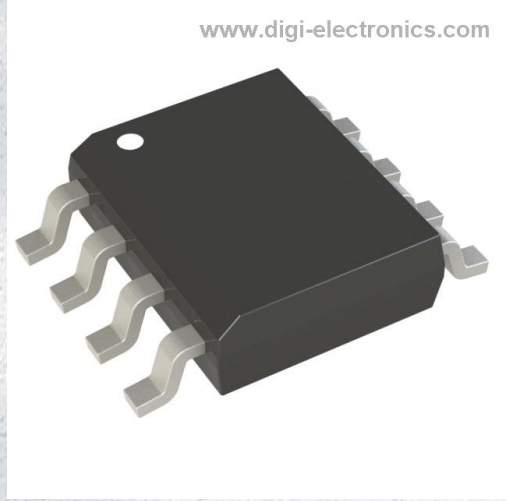
SI4831BDY-T1-GE3 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	SI4831BDY-T1-GE3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SI4831BDY-T1-GE3
Description	MOSFET P-CH 30V 6.6A 8SO
Detailed Description	P-Channel 30 V 6.6A (Tc) 2W (Ta), 3.3W (Tc) Surface Mount 8-SOIC

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SI4831BDY-T1-GE3	Vishay Siliconix
Series:	Product Status:
LITTLE FOOT®	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	6.6A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	42mOhm @ 5A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	26 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	625 pF @ 15 V
FET Feature:	Power Dissipation (Max):
Schottky Diode (Isolated)	2W (Ta), 3.3W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-SOIC	8-SOIC (0.154", 3.90mm Width)
Base Product Number:	
SI4831	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Si4831BDY

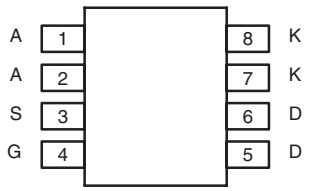
Vishay Siliconix

P-Channel 30-V (D-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
- 30	0.042 at V_{GS} = - 10 V	- 6.6	7.8
	0.065 at V_{GS} = - 4.5 V	- 5.3	

SCHOTTKY PRODUCT SUMMARY		
V_{KA} (V)	V_F (V) Diode Forward Voltage	I_D (A)[a]
30	0.53 V at 3 A	3.0

SO-8



Top View

Ordering Information: Si4831BDY-T1-E3 (Lead (Pb)-free)
Si4831BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

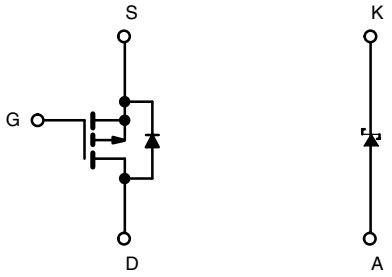
FEATURES

- **Halogen-free According to IEC 61249-2-21 Available**
- LITTLE FOOT® *Plus* Power MOSFET
- 100 % R_g Tested

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- HDD
- Asynchronous Rectification



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage (MOSFET)		V_{DS}	- 30	V
Reverse Voltage (Schottky)		V_{KA}	- 30	
Gate-Source Voltage (MOSFET)		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C) (MOSFET)	T_C = 25 °C	I_D	- 6.6	A
	T_C = 70 °C		- 5.2	
	T_A = 25 °C		- 5.1[b, c]	
	T_A = 70 °C		- 3.9[b, c]	
Pulsed Drain Current (MOSFET)		I_{DM}	- 30	
Continuous Source Current (MOSFET Diode Conduction)	T_C = 25 °C	I_S	- 2.7	
	T_A = 25 °C		- 1.6[b, c]	
Average Forward Current (Schottky)		I_F	- 3[b]	
Pulsed Forward Current (Schottky)		I_{FM}	- 20	
Maximum Power Dissipation (MOSFET and Schottky)	T_C = 25 °C	P_D	3.3	W
	T_C = 70 °C		2.1	
	T_A = 25 °C		2.0[b, c]	
	T_A = 70 °C		1.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient (MOSFET and Schottky)[b, c, d]	R_{thJA}	53	62.5	°C/W
Maximum Junction-to-Foot (Drain) (MOSFET and Schottky)	R_{thJF}	30	37	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on FR4 board.
c. t ≤ 10 s.
d. Maximum under Steady State conditions is 110 °C/W.

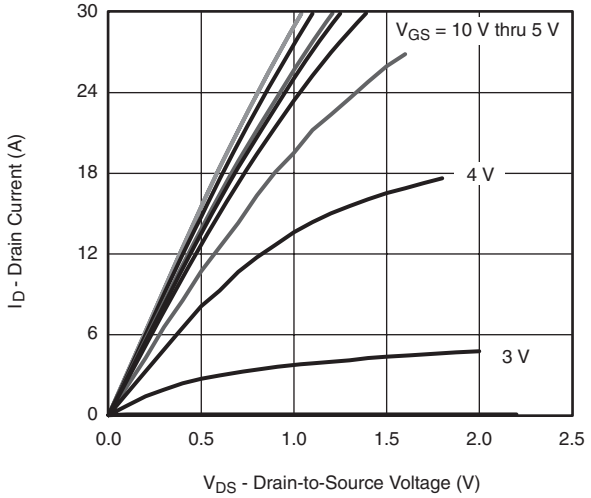
MOSFET SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = - 250 µA	- 30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS/TJ}$	I_D = 250 µA		- 30		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)/TJ}$			3.6		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 30 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 30 V, V_{GS} = 0 V, T_J = 75 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ - 5 V, V_{GS} = - 10 V	- 10			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 5 A		0.034	0.042	Ω
		V_{GS} = - 4.5 V, I_D = - 3 A		0.052	0.065	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 5 A		11		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 15 V, V_{GS} = 0 V, f = 1 MHz		625		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			115		
Total Gate Charge	Q_g	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 5 A		17	26	nC
		V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_D = - 5 A		7.8	12	
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			3.5		
Gate Resistance	R_g	f = 1 MHz		7	14	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 3 Ω $I_D \cong$ - 5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		35	55	ns
Rise Time	t_r			100	150	
Turn-Off Delay Time	$t_{d(off)}$			22	35	
Fall Time	t_f			12	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 3 Ω $I_D \cong$ - 5 A, V_{GEN} = - 10 V, R_g = 1 Ω		8	16	
Rise Time	t_r			8	16	
Turn-Off Delay Time	$t_{d(off)}$			24	40	
Fall Time	t_f			7	14	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C			- 3.3	A
Pulse Diode Forward Current[a]	I_{SM}				- 30	
Body Diode Voltage	V_{SD}	I_S = - 1.4 A, V_{GS} = 0 V		- 0.78	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 2 A, dI/dt = 100 A/µs, T_J = 25 °C		30	45	ns
Body Diode Reverse Recovery Charge	Q_{rr}			15	25	nC
Reverse Recovery Fall Time	t_a			14		ns
Reverse Recovery Rise Time	t_b			16		

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

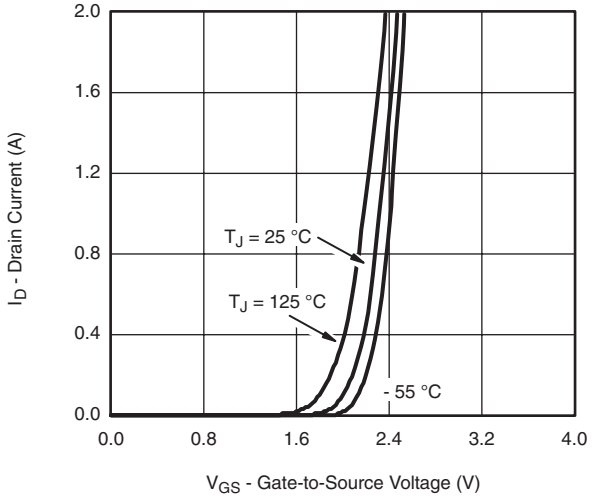
SCHOTTKY SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Forward Voltage Drop	V_F	I_F = 3 A		0.485	0.53	V
		I_F = 3 A, T_J = 125 °C		0.42	0.47	
Maximum Reverse Leakage Current	I_{rm}	V_R = 30 V		0.008	0.1	mA
		V_R = 30 V, T_J = 75 °C		0.4	5	
		V_R = 30 V, T_J = 125 °C		6.5	20	
Junction Capacitance	C_T	V_R = 15 V		102		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

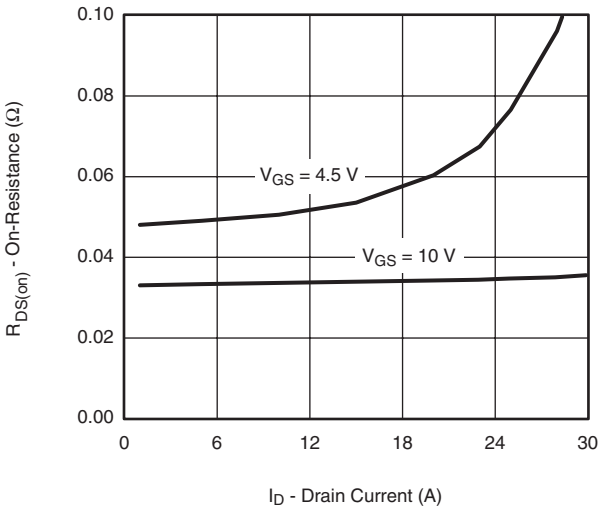
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



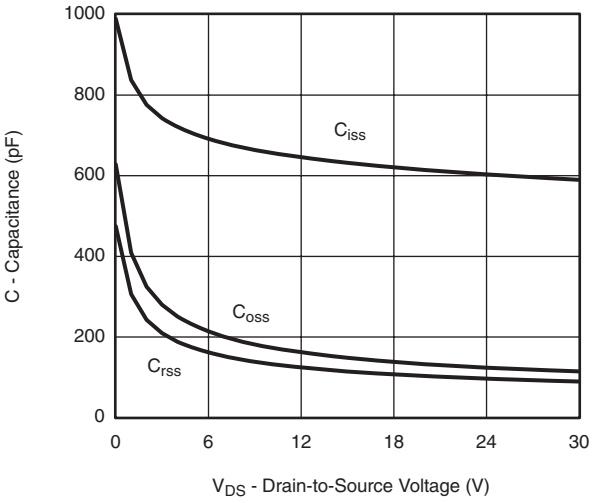
Output Characteristics



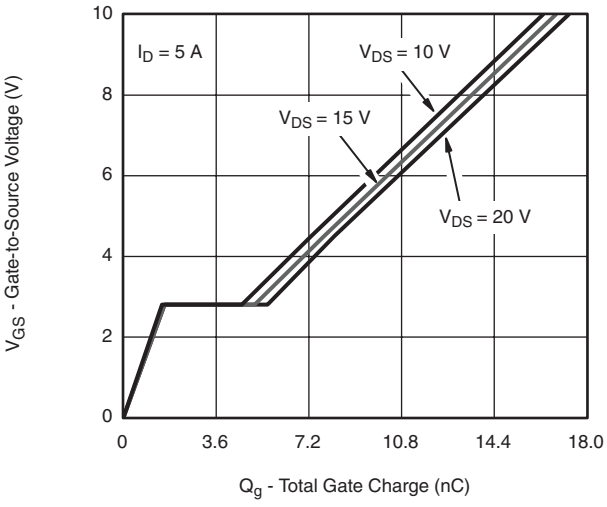
Transfer Characteristics



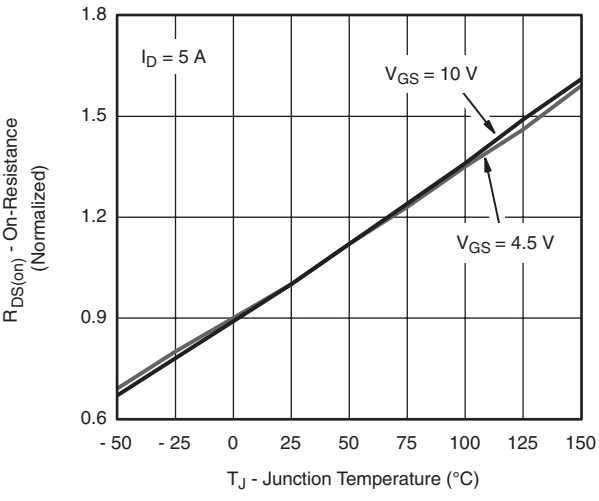
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

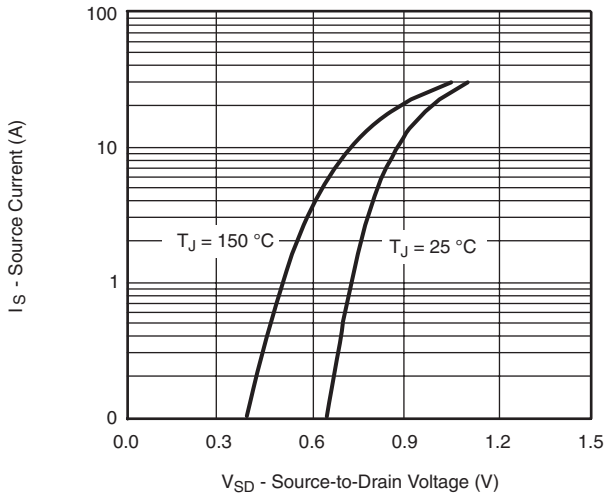


Gate Charge

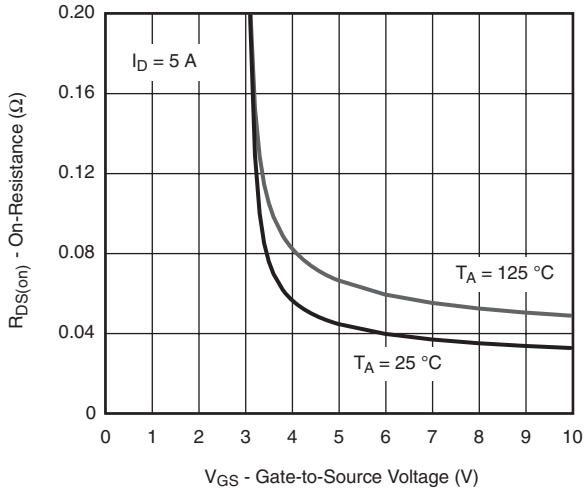


On-Resistance vs. Junction Temperature

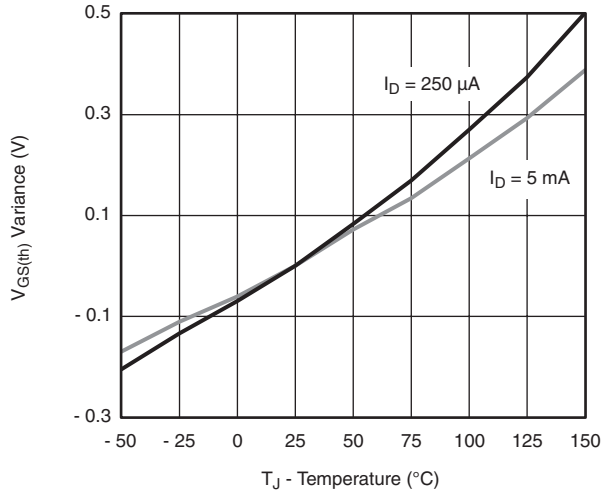
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



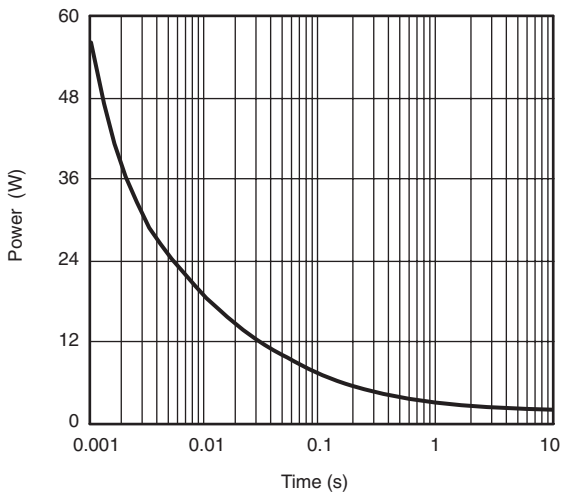
Source-Drain Diode Forward Voltage



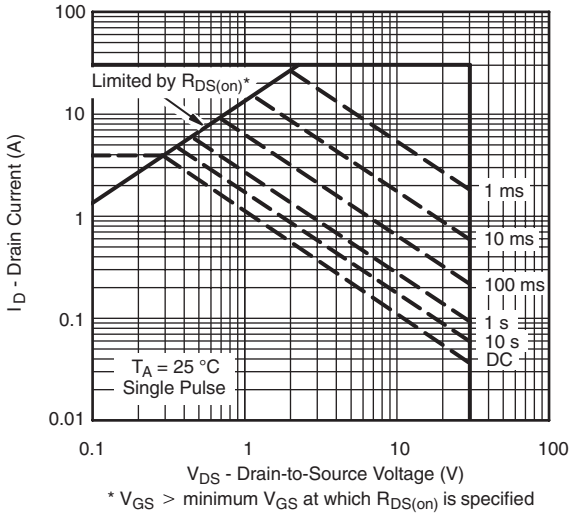
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



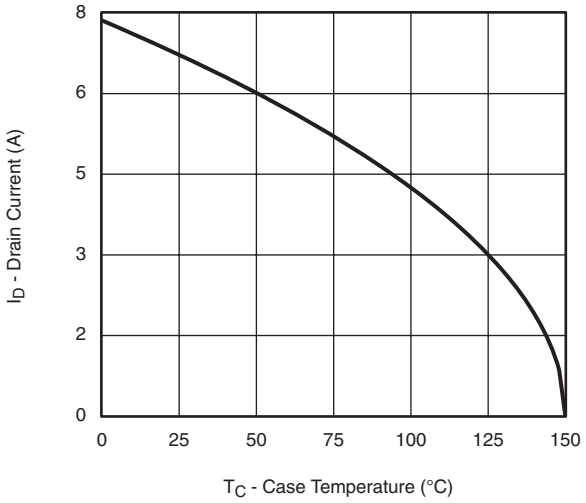
Single Pulse Power, Junction-to-Ambient



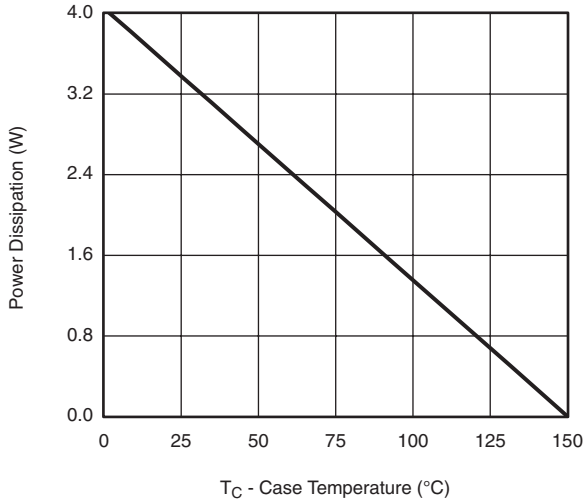
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

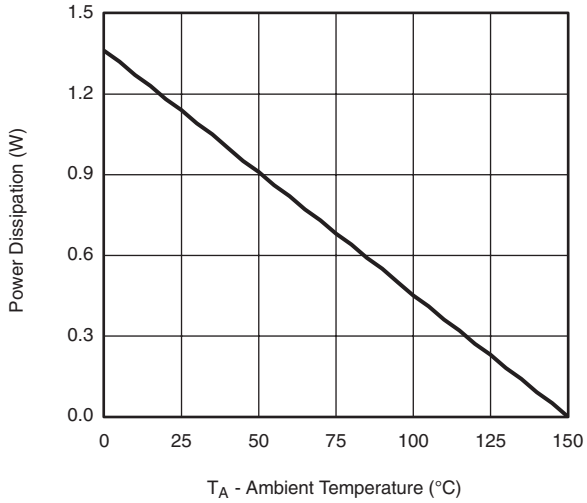
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



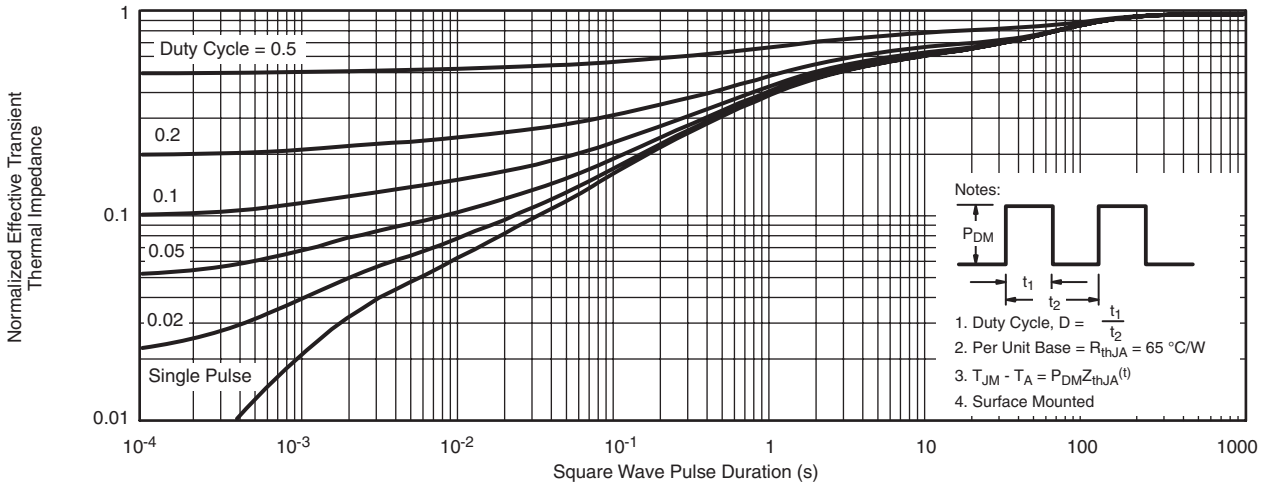
Power Derating, Junction-to-Foot



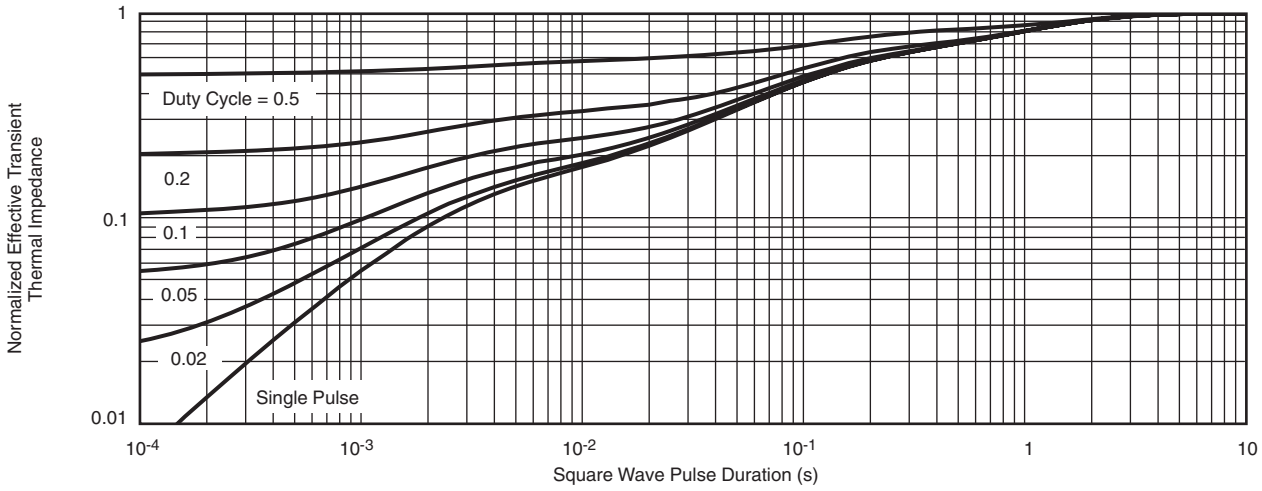
Power Derating, Junction-to-Ambient

* The power dissipation PD is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFETS TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

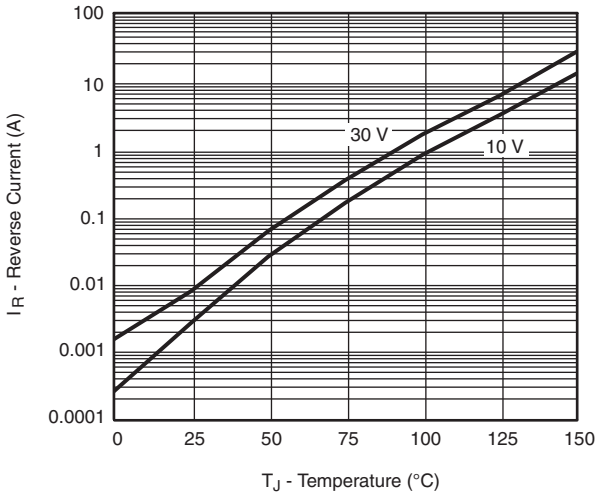


Normalized Thermal Transient Impedance, Junction-to-Ambient

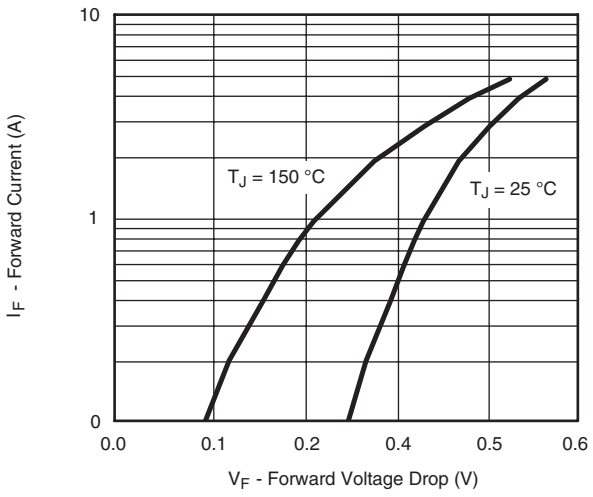


Normalized Thermal Transient Impedance, Junction-to-Foot

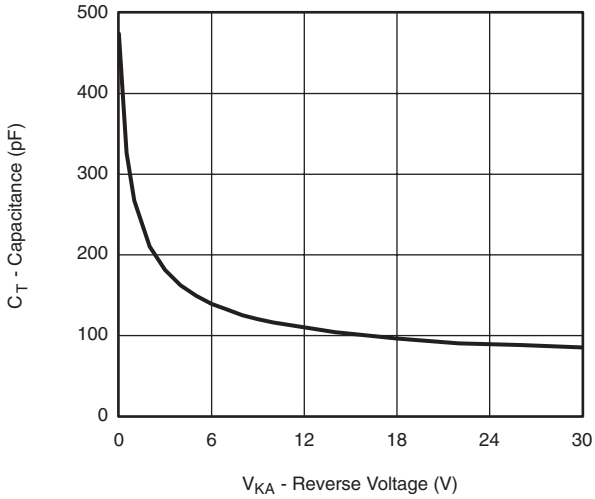
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop



Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70483.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

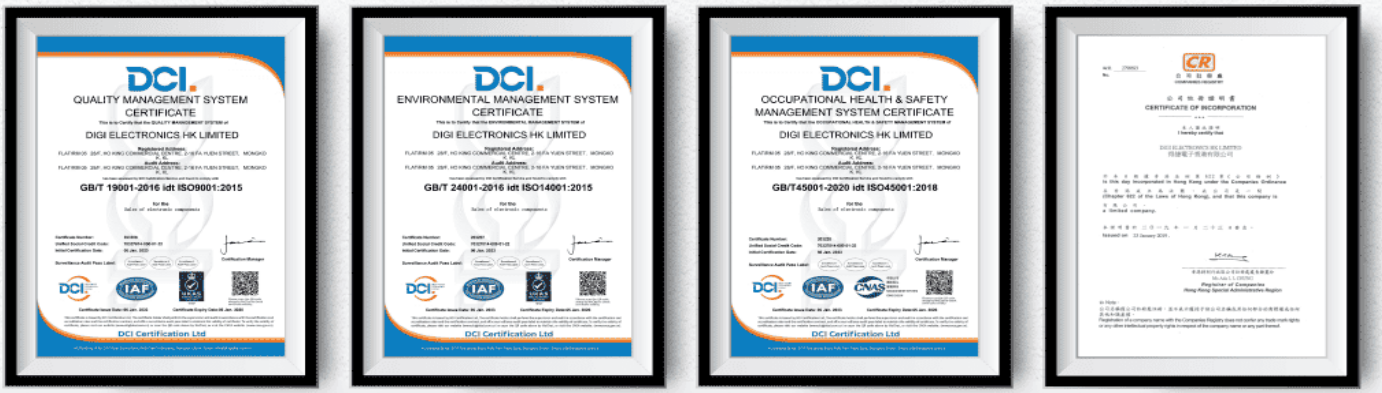
Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.